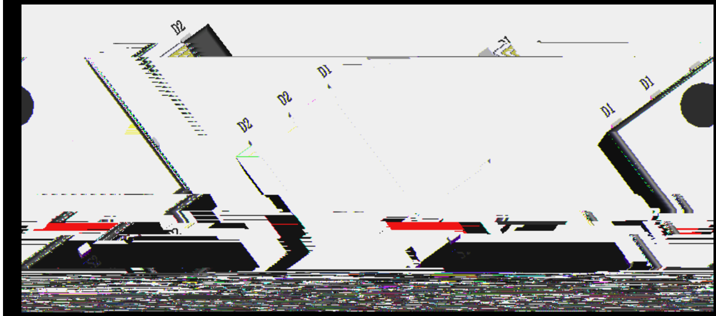
RoHS
COMPLIANT



Drain-source Voltage		V_{DS}	100	-100	V
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	T_C=25		40	-12	

c	T_A=25	P_D	2.5	2.5	W
	T_A=100		1	1	
	T_C=25		104	69	
	T_C =100		41	27	
Junction and Storage Temperature Range		T_J ,T_{STG}	-55 +150	-55 +150	

■Thermal resistance

Parameter		Symbol	NMOS		PMOS		Units
			Typ	Max	Typ	Max	
Thermal Resistance Junction-to-Ambient [D]	Steady-State	$R_{\theta JA}$	40	50	40	50	/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1	1.2	1.5	1.8	

[redacted]

■ NMOS Typical Electrical and Thermal Characteristics Diagrams

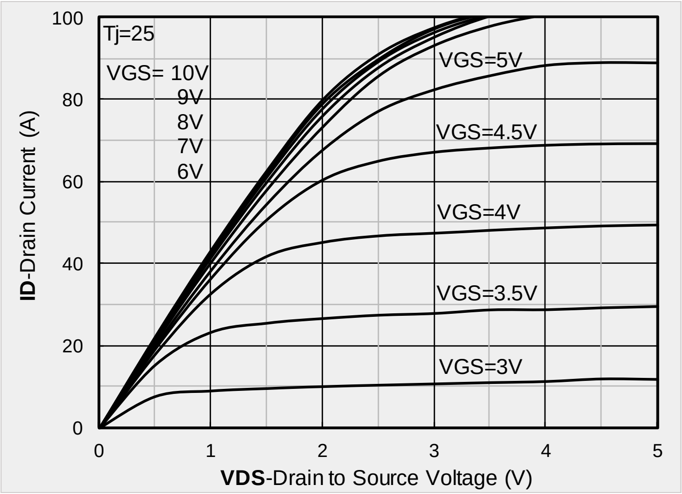


Figure 1. Output Characteristics

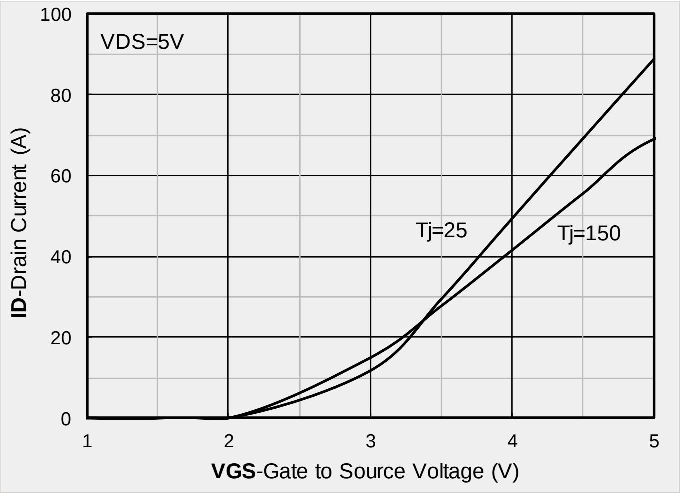
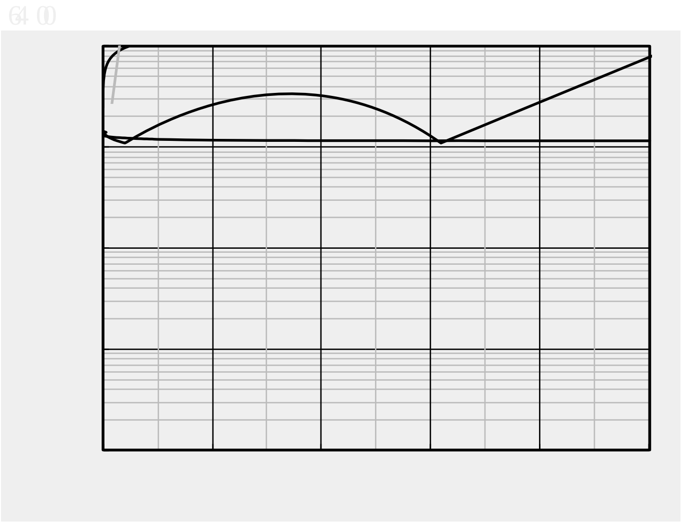


Figure 2. Transfer Characteristics



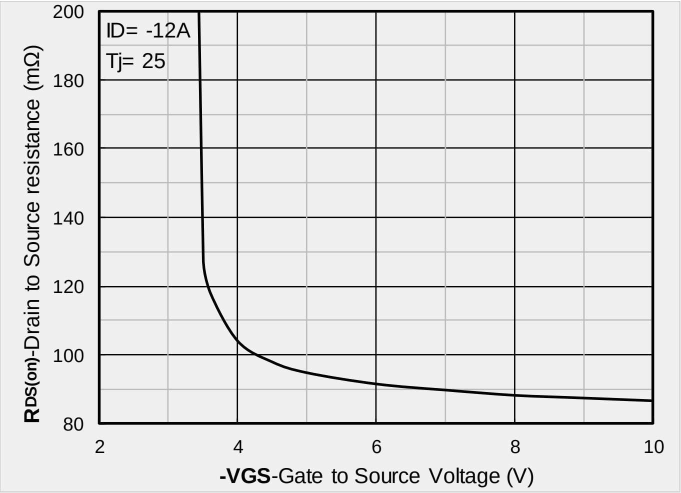


Figure 5. On-Resistance vs Gate to Source Voltage

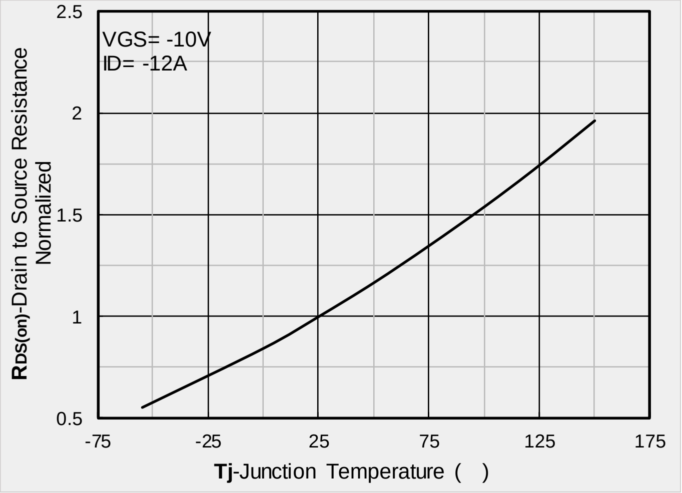
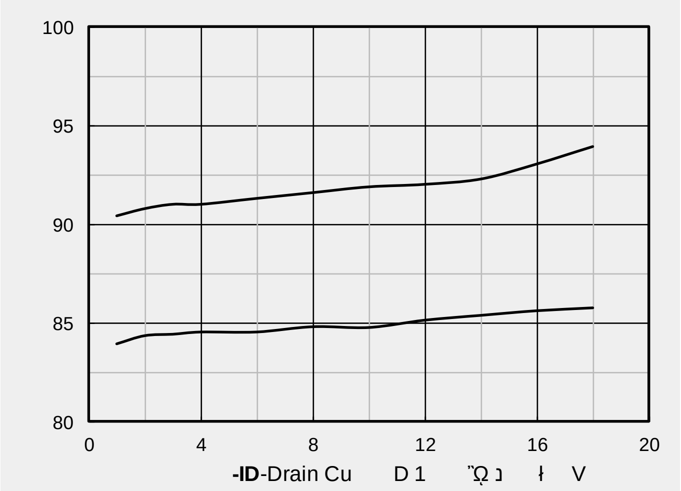
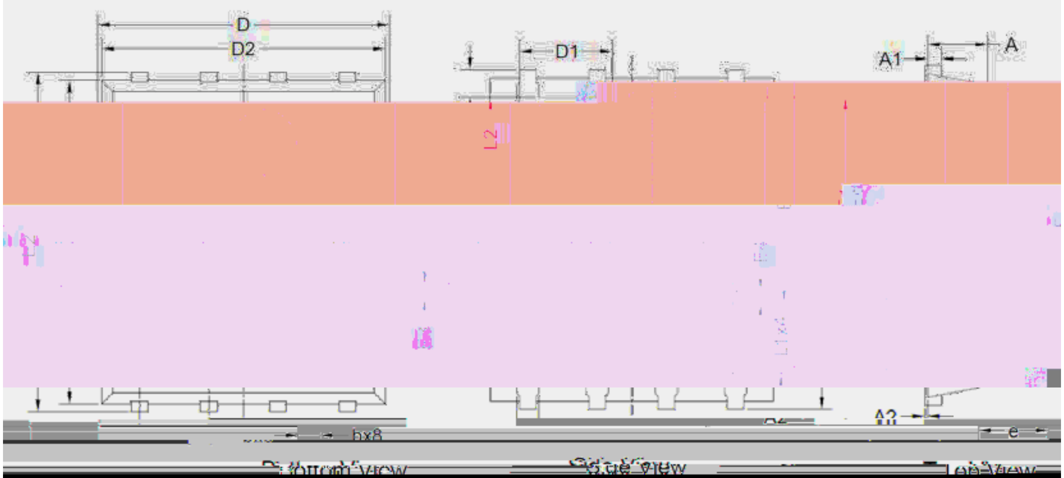


Figure 6. Normalized On-Resistance

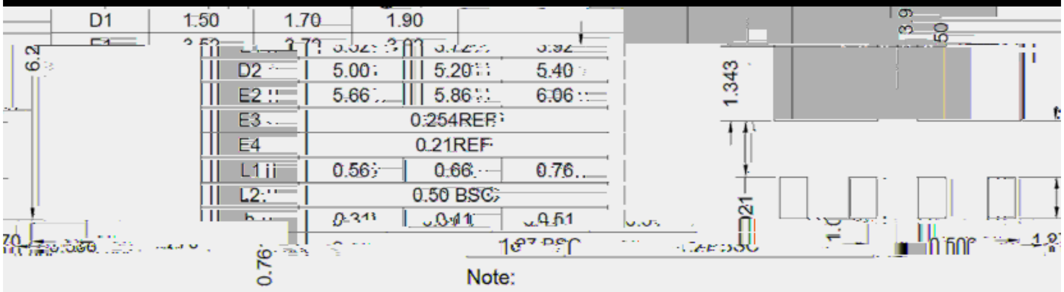


■ PDFN5060-8L Package information



[redacted]

D1	1.50	1.70	1.90
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254REF		
E4	0.21REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		



Suggested Solder Pad Layout

Top View

Note:

1. Controlling dimension is millimeters.

2. General tolerance ±0.10mm.

3. The pad layout is for reference purposes only.

Disclaimer

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